



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > 50V$
- $I_C = 1A$ High Continuous Current
- High Gain
- $R_{SAT} = 160m\Omega$ for Low Equivalent On Resistance
- Low Saturation Voltage $V_{CE(sat)} < -270mV @ 1A$

Mechanical Data

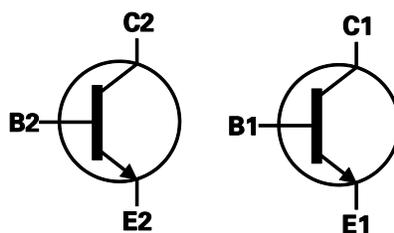
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 
- Weight: 0.015 grams (Approximate)

Applications

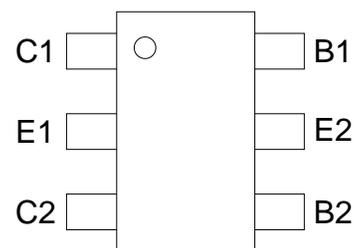
- LCD Backlighting Inverter Circuits
- Boost Functions in DC-DC Converters



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings – Q1 & Q2 Common (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	1	A
Peak Pulse Current	I _{CM}	2	A
Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

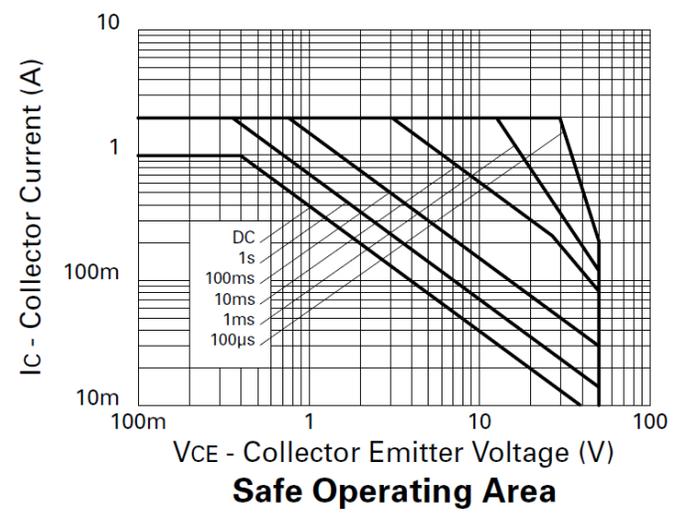
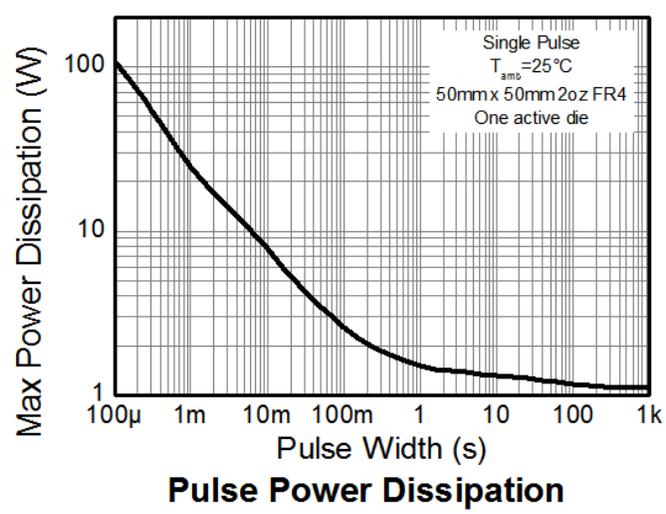
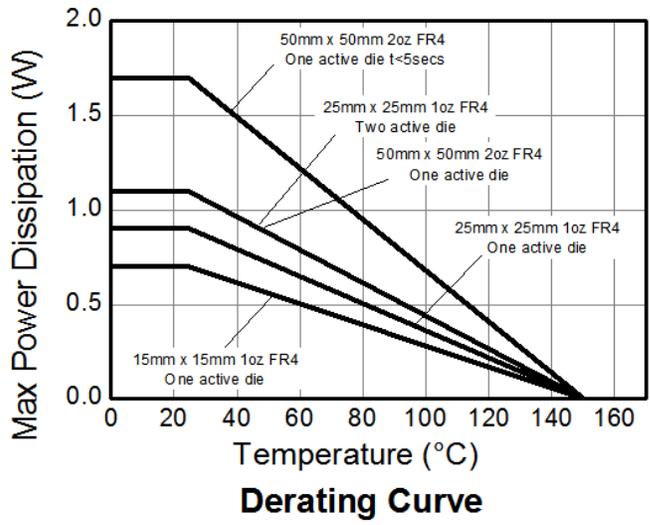
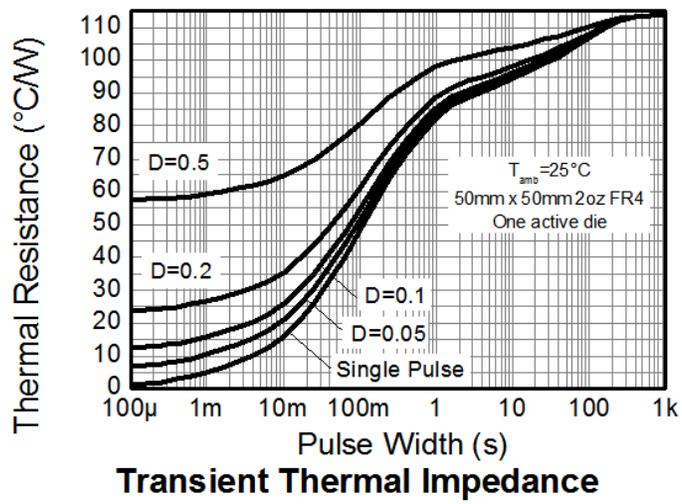
Characteristic	Symbol	Value	Unit	
Power Dissipation Linear Derating Factor	P _D	0.7	W mW/°C	
		5.6		
		0.9		
		7.2		
		1.1		
		8.8		
Thermal Resistance, Junction to Ambient	R _{θJA}	1.1	°C/W	
		8.8		
		1.7		
		13.6		
		179		
Thermal Resistance, Junction to Lead	R _{θJL}	139	°C/W	
		113		
		113		
		73		
Thermal Resistance, Junction to Lead	(Note 12)	R _{θJL}	95.50	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 13)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as Note 6, except the device is surface mounted on 25mm x 25mm 1oz copper.
 8. Same as Note 6, except the device is surface mounted on 50mm x 50mm 2oz copper.
 9. Same as Note 8, except the device is measured at t < 5 seconds.
 10. For device with one active die, both collectors attached to a common heatsink.
 11. For device with two active dice running at equal power, split heatsink 50% to each collector.
 12. Thermal resistance from junction to solder-point (at the end of the collector lead).
 13. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

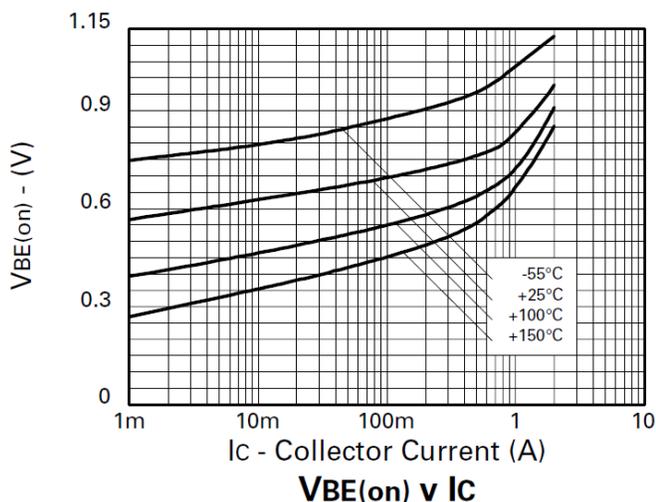
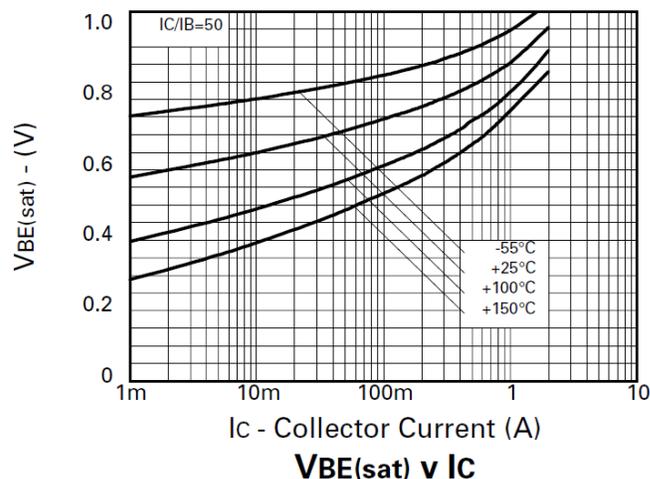
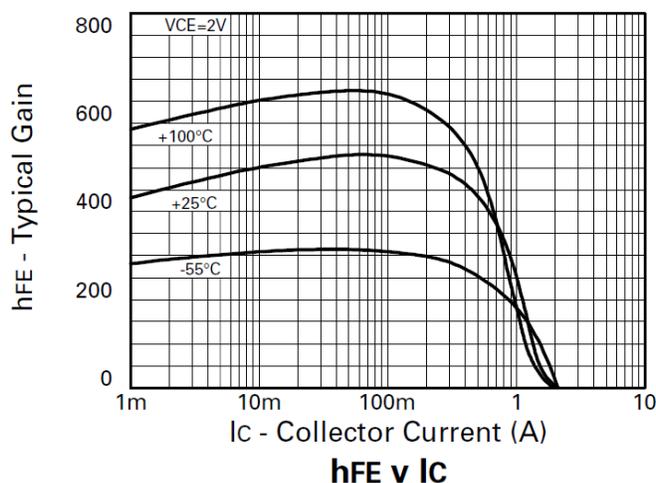
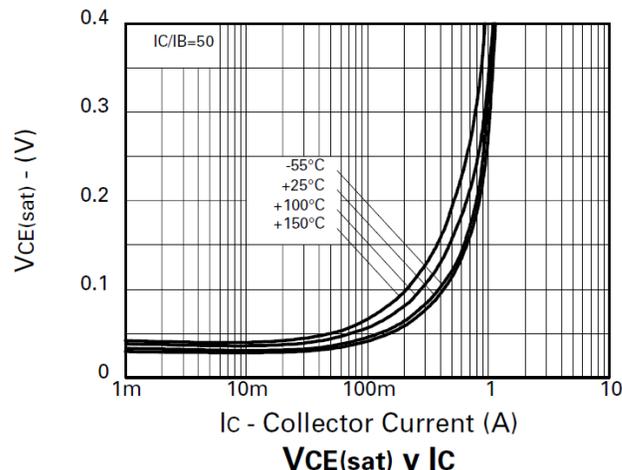
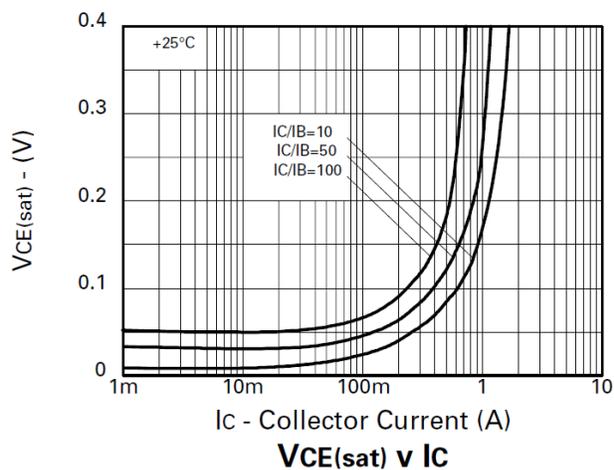


Electrical Characteristics - Q1 & Q2 common (@T_A = +25°C, unless otherwise specified.)

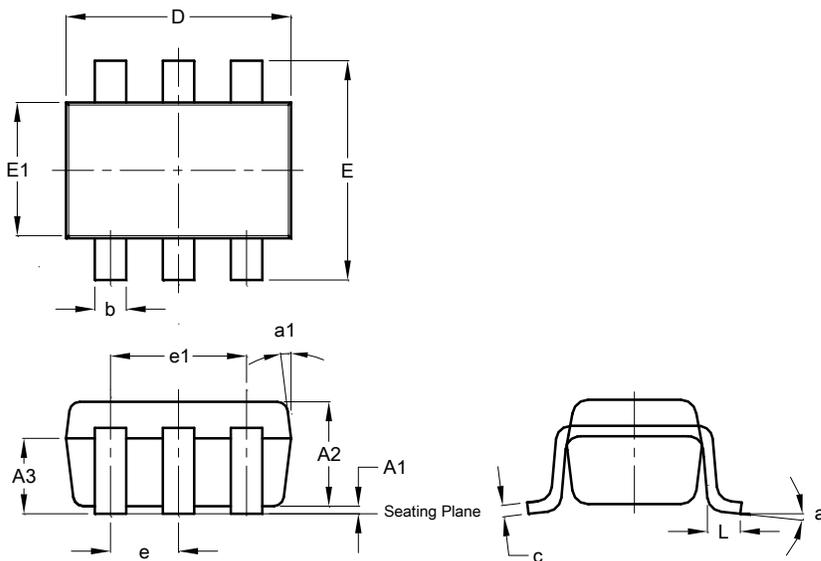
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 13)	BV _{CEO}	50	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	—	—	10	nA	V _{CB} = 40V
Collector-Emitter Cut-Off Current	I _{CES}	—	—	10	nA	V _{CES} = 40V
Emitter Cutoff Current	I _{EBO}	—	—	10	nA	V _{EB} = 5.6V
DC Current Gain (Note 13)	h _{FE}	200 300 200 75 20	420 450 350 130 60	—	—	I _C = 10mA, V _{CE} = 2V I _C = 100mA, V _{CE} = 2V I _C = 500mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 1.5A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 13)	V _{CE(sat)}	—	24 60 120 160	35 80 200 270	mV	I _C = 100mA, I _B = 10mA I _C = 250mA, I _B = 10mA I _C = 500mA, I _B = 10mA I _C = 1A, I _B = 50mA
Base-Emitter Saturation Voltage (Note 13)	V _{BE(sat)}	—	940	1100	mV	I _C = 1A, I _B = 50mA
Base-Emitter Turn-On Voltage (Note 13)	V _{BE(on)}	—	850	1100	mV	I _C = 1A, V _{CE} = 2V
Output Capacitance	C _{obo}	—	10	—	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	—	215	—	MHz	V _{CE} = 10V, I _C = 50mA f = 100MHz
Turn-On Time	t _{on}	—	150	—	ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _{off}	—	425	—	ns	I _{B1} = I _{B2} = 100mA

Note: 13. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

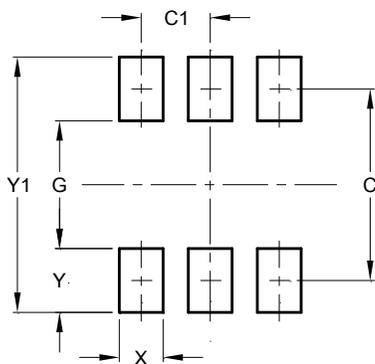


Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20